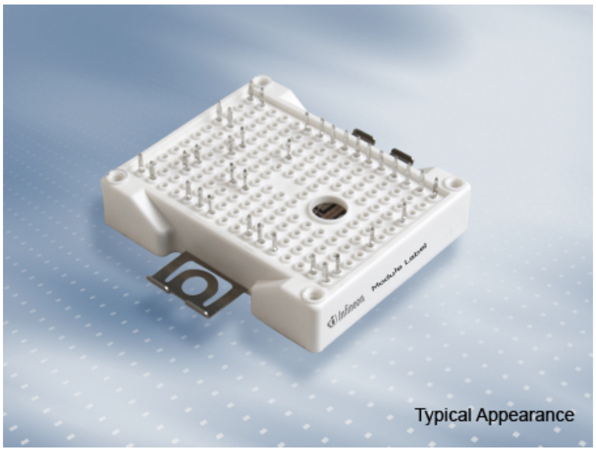
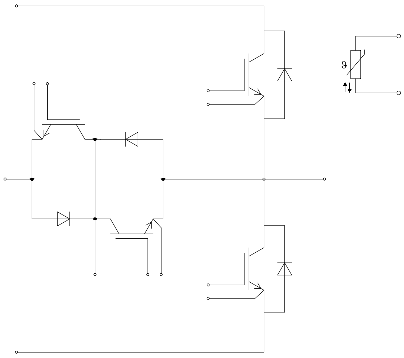
技术信息 / Technical Information

IGBT-模块
IGBT-Module

F3L200R12W2H3_B11

EasyPACK 模块 采用第二类中点钳位拓扑 (NPC2) 带有pressfit压接管脚和温度检测NTC
EasyPACK module with active "Neutral Point Clamp 2" topology and PressFIT / NTC





V_{CES} = 1200V
$I_{C\ nom}$ = 100A / I_{CRM} = 200A

典型应用
- 三电平应用
- 电机传动
- 太阳能应用
- UPS系统

Typical Applications
- 3-level-applications
- Motor drives
- Solar applications
- UPS systems

电气特性
- 高速IGBT H3
- 低开关损耗
- $T_{vj\ op}$ = 150°C

Electrical Features
- High speed IGBT H3
- Low switching losses
- $T_{vj\ op}$ = 150°C

机械特性
- 3 kV 交流 1分钟 绝缘
- PressFIT 压接技术
- 符合RoHS

Mechanical Features
- 3 kV AC 1min insulation
- PressFIT contact technology
- RoHS compliant

Module Label Code

Barcode Code 128

Sample
0000012345600000000000

DMX - Code

Sample

Content of the Code	Digit
Module Serial Number	1 - 5
Module Material Number	6 - 11
Production Order Number	12 - 19
Datecode (Production Year)	20 - 21
Datecode (Production Week)	22 - 23

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IGBT, T1 / T4 / IGBT, T1 / T4

最大额定值 / Maximum Rated Values

集电极 - 发射极电压 Collector-emitter voltage	T_{vj} = 25°C	V_{CES}	1200	V
集电极电流 Implemented collector current		I_{CN}	200	A
连续集电极直流电流 Continuous DC collector current	T_C = 100°C, $T_{vj\,max}$ = 175°C	$I_{C\,nom}$	100	A
集电极重复峰值电流 Repetitive peak collector current	t_P = 1 ms	I_{CRM}	400	A
总功率损耗 Total power dissipation	T_C = 25°C, $T_{vj\,max}$ = 175°C	P_{tot}	600	W
栅极 - 发射极峰值电压 Gate-emitter peak voltage		V_{GES}	+/-20	V

特征值 / Characteristic Values

				min.	typ.	max.	
集电极 - 发射极饱和电压 Collector-emitter saturation voltage	I_C = 100 A, V_{GE} = 15 V I_C = 100 A, V_{GE} = 15 V I_C = 100 A, V_{GE} = 15 V	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	$V_{CE\,sat}$		1,55 1,70 1,75	1,75	V V V
栅极阈值电压 Gate threshold voltage	I_C = 7,60 mA, V_{CE} = V_{GE}, T_{vj} = 25°C		V_{GEth}	5,05	5,80	6,45	V
栅极电荷 Gate charge	V_{GE} = -15 V ... +15 V		Q_G		1,60		µC
内部栅极电阻 Internal gate resistor	T_{vj} = 25°C		R_{Gint}		3,8		Ω
输入电容 Input capacitance	f = 1 MHz, T_{vj} = 25°C, V_{CE} = 25 V, V_{GE} = 0 V		C_{ies}		11,5		nF
反向传输电容 Reverse transfer capacitance	f = 1 MHz, T_{vj} = 25°C, V_{CE} = 25 V, V_{GE} = 0 V		C_{res}		0,70		nF
集电极-发射极截止电流 Collector-emitter cut-off current	V_{CE} = 1200 V, V_{GE} = 0 V, T_{vj} = 25°C		I_{CES}			1,0	mA
栅极-发射极漏电流 Gate-emitter leakage current	V_{CE} = 0 V, V_{GE} = 20 V, T_{vj} = 25°C		I_{GES}			100	nA
开通延迟时间(电感负载) Turn-on delay time, inductive load	I_C = 100 A, V_{CE} = 400 V V_{GE} = ±15 V R_{Gon} = 1,1 Ω	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	$t_{d\,on}$		0,14 0,155 0,16		µs µs µs
上升时间(电感负载) Rise time, inductive load	I_C = 100 A, V_{CE} = 400 V V_{GE} = ±15 V R_{Gon} = 1,1 Ω	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	t_r		0,025 0,03 0,03		µs µs µs
关断延迟时间(电感负载) Turn-off delay time, inductive load	I_C = 100 A, V_{CE} = 400 V V_{GE} = ±15 V R_{Goff} = 1,1 Ω	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	$t_{d\,off}$		0,32 0,40 0,42		µs µs µs
下降时间(电感负载) Fall time, inductive load	I_C = 100 A, V_{CE} = 400 V V_{GE} = ±15 V R_{Goff} = 1,1 Ω	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	t_f		0,03 0,055 0,06		µs µs µs
开通损耗能量 (每脉冲) Turn-on energy loss per pulse	I_C = 100 A, V_{CE} = 400 V, L_S = 25 nH V_{GE} = ±15 V, di/dt = 3700 A/µs (T_{vj} = 150°C) R_{Gon} = 1,1 Ω	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	E_{on}		1,20 2,00 2,25		mJ mJ mJ
关断损耗能量 (每脉冲) Turn-off energy loss per pulse	I_C = 100 A, V_{CE} = 400 V, L_S = 25 nH V_{GE} = ±15 V, du/dt = 2700 V/µs (T_{vj} = 150°C) R_{Goff} = 1,1 Ω	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	E_{off}		3,50 5,30 5,90		mJ mJ mJ
短路数据 SC data	V_{GE} ≤ 15 V, V_{CC} = 800 V V_{CEmax} = V_{CES} -L_{sCE} ·di/dt	t_P ≤ 10 µs, T_{vj} = 150°C	I_{SC}		800		A
结 - 外壳热阻 Thermal resistance, junction to case	每个 IGBT / per IGBT		R_{thJC}		0,200	0,250	K/W

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外壳 - 散热器热阻 Thermal resistance, case to heatsink	每个 IGBT / per IGBT λ_{Paste} = 1 W/(m·K) / λ_{grease} = 1 W/(m·K)	R_{thCH}		0,200		K/W
在开关状态下温度 Temperature under switching conditions		$T_{vj\ op}$	-40		150	°C

二极管, D2 / D3 / Diode, D2 / D3

最大额定值 / Maximum Rated Values

反向重复峰值电压 Repetitive peak reverse voltage	T_{vj} = 25°C	V_{RRM}	650	V
正向电流 Implemented forward current		I_{FN}	125	A
连续正向直流电流 Continuous DC forward current		I_F	100	A
正向重复峰值电流 Repetitive peak forward current	t_P = 1 ms	I_{FRM}	250	A
I2t-值 I²t - value	V_R = 0 V, t_P = 10 ms, T_{vj} = 125°C V_R = 0 V, t_P = 10 ms, T_{vj} = 150°C	I^2t	1450 1400	A²s A²s

特征值 / Characteristic Values

				min.	typ.	max.	
正向电压 Forward voltage	I_F = 100 A, V_{GE} = 0 V I_F = 100 A, V_{GE} = 0 V I_F = 100 A, V_{GE} = 0 V	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	V_F		1,55 1,50 1,45	1,70	V V V
反向恢复峰值电流 Peak reverse recovery current	I_F = 100 A, - di_F/dt = 3700 A/µs (T_{vj}=150°C) V_R = 400 V V_{GE} = -15 V	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	I_{RM}		90,0 100 100		A A A
恢复电荷 Recovered charge	I_F = 100 A, - di_F/dt = 3700 A/µs (T_{vj}=150°C) V_R = 400 V V_{GE} = -15 V	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	Q_r		3,25 5,90 6,40		µC µC µC
反向恢复损耗（每脉冲） Reverse recovery energy	I_F = 100 A, - di_F/dt = 3700 A/µs (T_{vj}=150°C) V_R = 400 V V_{GE} = -15 V	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	E_{rec}		0,95 1,55 1,65		mJ mJ mJ
结 - 外壳热阻 Thermal resistance, junction to case	每个二极管 / per diode		R_{thJC}		0,550	0,650	K/W
外壳 - 散热器热阻 Thermal resistance, case to heatsink	每个二极管 / per diode λ_{Paste} = 1 W/(m·K) / λ_{grease} = 1 W/(m·K)		R_{thCH}		0,600		K/W
在开关状态下温度 Temperature under switching conditions			$T_{vj\ op}$	-40		150	°C

IGBT, T2 / T3 / IGBT, T2 / T3

最大额定值 / Maximum Rated Values

集电极 - 发射极电压 Collector-emitter voltage	T_{vj} = 25°C	V_{CES}	650	V
连续集电极直流电流 Continuous DC collector current	T_C = 100°C, $T_{vj\ max}$ = 175°C	$I_{C\ nom}$	100	A
集电极重复峰值电流 Repetitive peak collector current	t_P = 1 ms	I_{CRM}	200	A
总功率损耗 Total power dissipation	T_C = 25°C, $T_{vj\ max}$ = 175°C	P_{tot}	250	W
栅极 - 发射极峰值电压 Gate-emitter peak voltage		V_{GES}	+/-20	V

特征值 / Characteristic Values

				min.	typ.	max.	
集电极 - 发射极饱和电压 Collector-emitter saturation voltage	I_C = 100 A, V_{GE} = 15 V I_C = 100 A, V_{GE} = 15 V I_C = 100 A, V_{GE} = 15 V	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	$V_{CE\ sat}$		1,45 1,60 1,70	1,90	V V V
栅极阈值电压 Gate threshold voltage	I_C = 1,60 mA, V_{CE} = V_{GE}, T_{vj} = 25°C		V_{GEth}	4,95	5,80	6,45	V
栅极电荷 Gate charge	V_{GE} = -15 V ... +15 V		Q_G		1,00		µC
内部栅极电阻 Internal gate resistor	T_{vj} = 25°C		R_{Gint}		2,0		Ω
输入电容 Input capacitance	f = 1 MHz, T_{vj} = 25°C, V_{CE} = 25 V, V_{GE} = 0 V		C_{ies}		6,20		nF
反向传输电容 Reverse transfer capacitance	f = 1 MHz, T_{vj} = 25°C, V_{CE} = 25 V, V_{GE} = 0 V		C_{res}		0,19		nF
集电极-发射极截止电流 Collector-emitter cut-off current	V_{CE} = 650 V, V_{GE} = 0 V, T_{vj} = 25°C		I_{CES}			1,0	mA
栅极-发射极漏电流 Gate-emitter leakage current	V_{CE} = 0 V, V_{GE} = 20 V, T_{vj} = 25°C		I_{GES}			100	nA
开通延迟时间(电感负载) Turn-on delay time, inductive load	I_C = 100 A, V_{CE} = 400 V V_{GE} = ±15 V R_{Gon} = 3,3 Ω	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	$t_{d\ on}$		0,055 0,06 0,065		µs µs µs
上升时间(电感负载) Rise time, inductive load	I_C = 100 A, V_{CE} = 400 V V_{GE} = ±15 V R_{Gon} = 3,3 Ω	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	t_r		0,025 0,03 0,03		µs µs µs
关断延迟时间(电感负载) Turn-off delay time, inductive load	I_C = 100 A, V_{CE} = 400 V V_{GE} = ±15 V R_{Goff} = 3,3 Ω	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	$t_{d\ off}$		0,25 0,27 0,28		µs µs µs
下降时间(电感负载) Fall time, inductive load	I_C = 100 A, V_{CE} = 400 V V_{GE} = ±15 V R_{Goff} = 3,3 Ω	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	t_f		0,035 0,05 0,06		µs µs µs
开通损耗能量 (每脉冲) Turn-on energy loss per pulse	I_C = 100 A, V_{CE} = 400 V, L_S = 25 nH V_{GE} = ±15 V, di/dt = 3800 A/µs (T_{vj} = 150°C) R_{Gon} = 3,3 Ω	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	E_{on}		1,85 2,80 3,30		mJ mJ mJ
关断损耗能量 (每脉冲) Turn-off energy loss per pulse	I_C = 100 A, V_{CE} = 400 V, L_S = 25 nH V_{GE} = ±15 V, du/dt = 4600 V/µs (T_{vj} = 150°C) R_{Goff} = 3,3 Ω	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	E_{off}		3,10 4,10 4,60		mJ mJ mJ
短路数据 SC data	$V_{GE} \leq$ 15 V, V_{CC} = 360 V V_{CEmax} = V_{CES} -L_{sCE} ·di/dt	$t_P \leq$ 8 µs, T_{vj} = 25°C $t_P \leq$ 6 µs, T_{vj} = 150°C	I_{SC}		700 500		A A
结 - 外壳热阻 Thermal resistance, junction to case	每个 IGBT / per IGBT		R_{thJC}		0,500	0,600	K/W
外壳 - 散热器热阻 Thermal resistance, case to heatsink	每个 IGBT / per IGBT λ_{Paste} = 1 W/(m·K) / λ_{grease} = 1 W/(m·K)		R_{thCH}		0,500		K/W
在开关状态下温度 Temperature under switching conditions			$T_{vj\ op}$	-40		150	°C

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二极管, D1 / D4 / Diode, D1 / D4

最大额定值 / Maximum Rated Values

反向重复峰值电压 Repetitive peak reverse voltage	T_{vj} = 25°C	V_{RRM}	1200	V
连续正向直流电流 Continuous DC forward current		I_F	75	A
正向重复峰值电流 Repetitive peak forward current	t_P = 1 ms	I_{FRM}	150	A
I2t-值 I^2t - value	V_R = 0 V, t_P = 10 ms, T_{vj} = 125°C V_R = 0 V, t_P = 10 ms, T_{vj} = 150°C	I^2t	1050 985	A^2s A^2s

特征值 / Characteristic Values

				min.	typ.	max.	
正向电压 Forward voltage	I_F = 75 A, V_{GE} = 0 V I_F = 75 A, V_{GE} = 0 V I_F = 75 A, V_{GE} = 0 V	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	V_F		1,65 1,65 1,65	2,15	V V V
反向恢复峰值电流 Peak reverse recovery current	I_F = 75 A, - di_F/dt = 3500 A/µs (T_{vj}=150°C) V_R = 400 V V_{GE} = -15 V	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	I_{RM}		120 140 150		A A A
恢复电荷 Recovered charge	I_F = 75 A, - di_F/dt = 3500 A/µs (T_{vj}=150°C) V_R = 400 V V_{GE} = -15 V	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	Q_r		8,50 17,0 19,0		µC µC µC
反向恢复损耗（每脉冲） Reverse recovery energy	I_F = 75 A, - di_F/dt = 3500 A/µs (T_{vj}=150°C) V_R = 400 V V_{GE} = -15 V	T_{vj} = 25°C T_{vj} = 125°C T_{vj} = 150°C	E_{rec}		2,85 5,70 6,30		mJ mJ mJ
结 - 外壳热阻 Thermal resistance, junction to case	每个二极管 / per diode		R_{thJC}		0,550	0,600	K/W
外壳 - 散热器热阻 Thermal resistance, case to heatsink	每个二极管 / per diode λ_{Paste} = 1 W/(m·K) / λ_{grease} = 1 W/(m·K)		R_{thCH}		0,500		K/W
在开关状态下温度 Temperature under switching conditions			$T_{vj\ op}$	-40		150	°C

模块 / Module

绝缘测试电压 Isolation test voltage	RMS, f = 50 Hz, t = 1 min.	V_{ISOL}	3,0	kV
内部绝缘 Internal isolation	基本绝缘 (class 1, IEC 61140) basic insulation (class 1, IEC 61140)		Al_2O_3	
爬电距离 Creepage distance	端子至散热器 / terminal to heatsink 端子至端子 / terminal to terminal		11,5 6,3	mm
电气间隙 Clearance	端子至散热器 / terminal to heatsink 端子至端子 / terminal to terminal		10,0 5,0	mm
相对电痕指数 Comperative tracking index		CTI	> 200	

			min.	typ.	max.	
杂散电感,模块 Stray inductance module		L_{sCE}		14		nH
储存温度 Storage temperature		T_{stg}	-40		125	°C
Anpresskraft für mech. Bef. pro Feder mountig force per clamp		F	40	-	80	N
重量 Weight		G		36		g

Der Strom im Dauerbetrieb ist auf 25A effektiv pro Anschlusspin begrenzt.
The current under continuous operation is limited to 25A rms per connector pin.

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负温度系数热敏电阻 / NTC-Thermistor

特征值 / Characteristic Values

			min.	typ.	max.	
额定电阻值 Rated resistance	T_{NTC} = 25°C	R_{25}		5,00		kΩ
R100 偏差 Deviation of R100	T_{NTC} = 100°C, R_{100} = 493 Ω	ΔR/R	-5		5	%
耗散功率 Power dissipation	T_{NTC} = 25°C	P_{25}			20,0	mW
B-值 B-value	$R_2 = R_{25} \exp [B_{25/50}(1/T_2 - 1/(298,15\ K))]$	$B_{25/50}$		3375		K
B-值 B-value	$R_2 = R_{25} \exp [B_{25/80}(1/T_2 - 1/(298,15\ K))]$	$B_{25/80}$		3411		K
B-值 B-value	$R_2 = R_{25} \exp [B_{25/100}(1/T_2 - 1/(298,15\ K))]$	$B_{25/100}$		3433		K

根据应用手册标定
Specification according to the valid application note.

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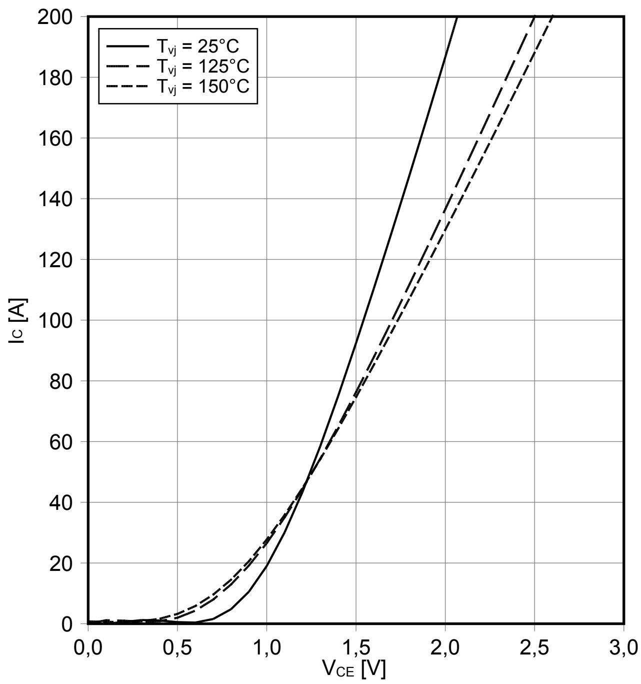
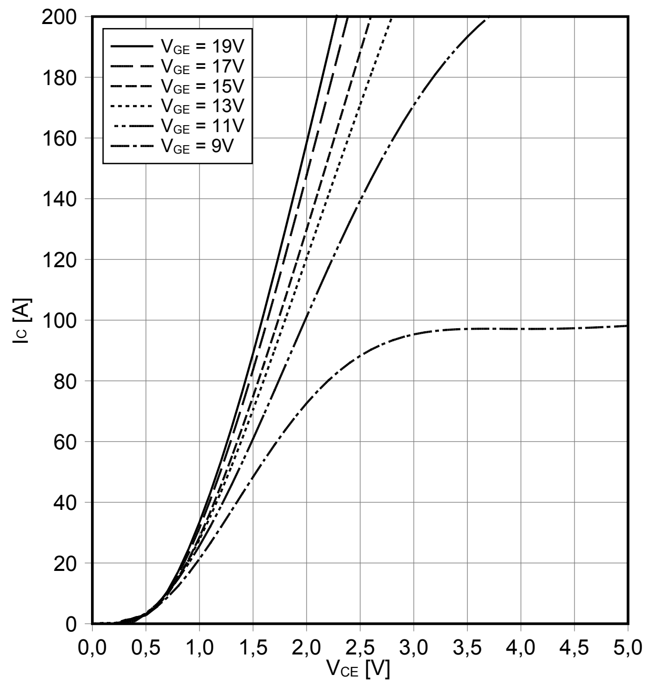
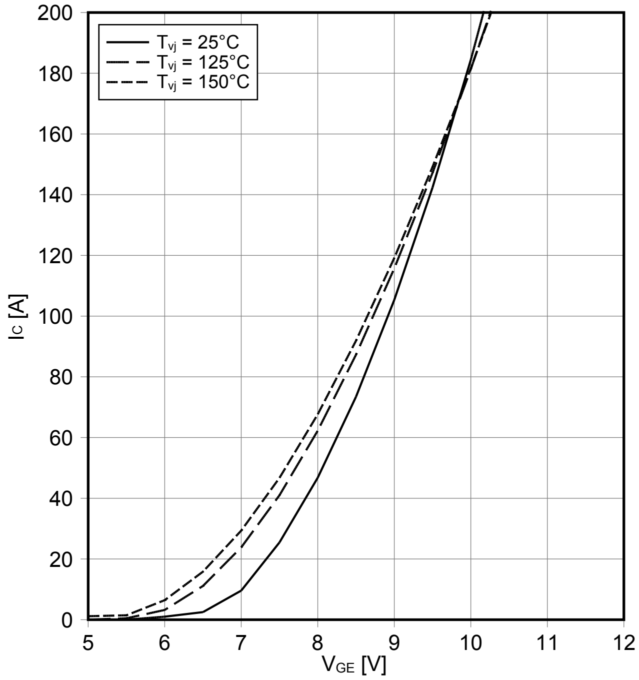
输出特性 IGBT, T1 / T4 (典型)
output characteristic IGBT, T1 / T4 (typical)
$I_C = f(V_{CE})$
$V_{GE} = 15$ V



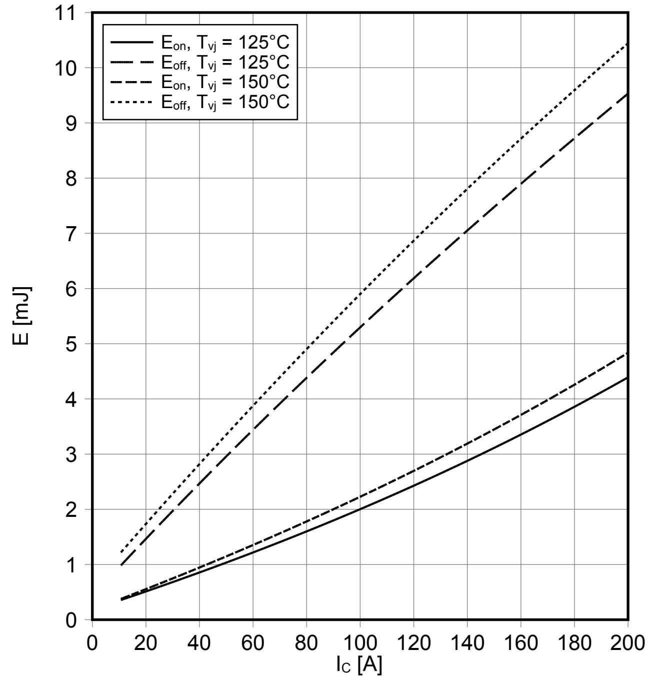
输出特性 IGBT, T1 / T4 (典型)
output characteristic IGBT, T1 / T4 (typical)
$I_C = f(V_{CE})$
$T_{vj} = 150$°C



传输特性 IGBT, T1 / T4 (典型)
transfer characteristic IGBT, T1 / T4 (typical)
$I_C = f(V_{GE})$
$V_{CE} = 20$ V



开关损耗 IGBT, T1 / T4 (典型)
switching losses IGBT, T1 / T4 (typical)
$E_{on} = f(I_C)$, $E_{off} = f(I_C)$
$V_{GE} = \pm 15$ V, $R_{Gon} = 1.1\ \Omega$, $R_{Goff} = 1.1\ \Omega$, $V_{CE} = 400$ V



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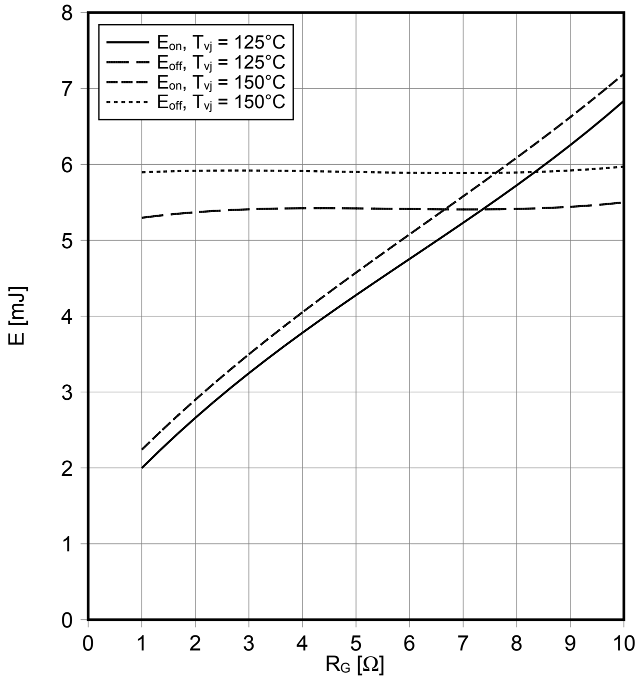
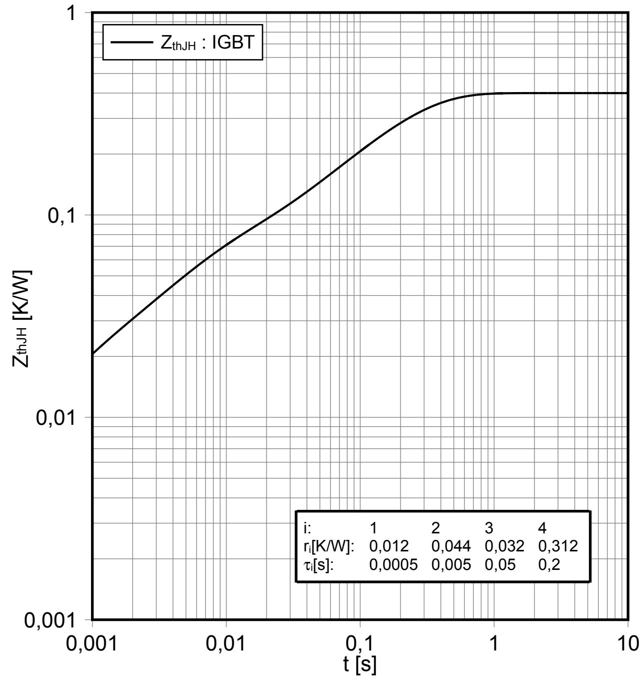
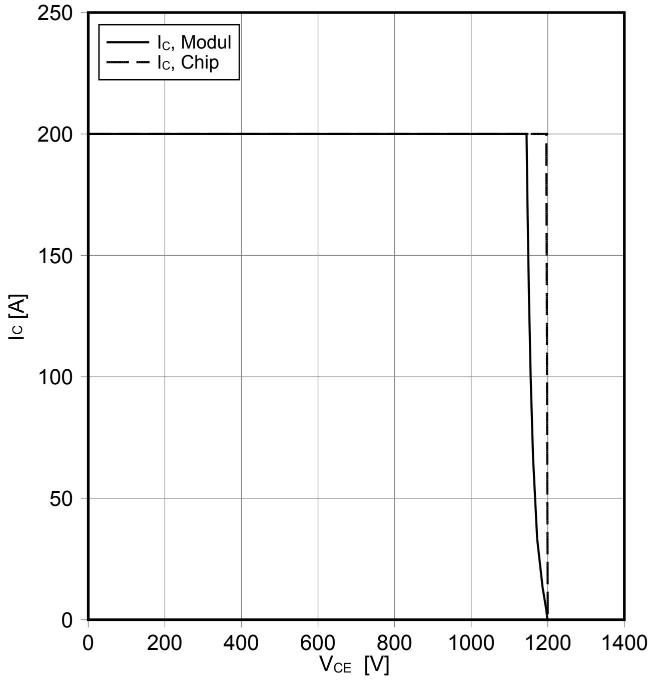
开关损耗 IGBT, T1 / T4 (典型)
switching losses IGBT, T1 / T4 (typical)
E_{on} = f (R_G), E_{off} = f (R_G)
V_{GE} = ±15 V, I_C = 100 A, V_{CE} = 400 V



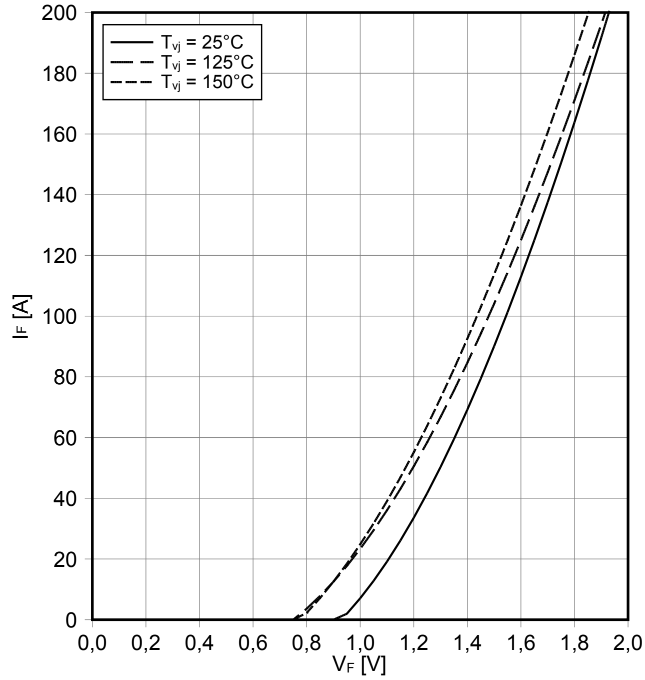
瞬态热阻抗 IGBT, T1 / T4
transient thermal impedance IGBT, T1 / T4
Z_{thJH} = f (t)



反偏安全工作区 IGBT, T1 / T4 (RBSOA)
reverse bias safe operating area IGBT, T1 / T4 (RBSOA)
I_C = f (V_{CE})
V_{GE} = ±15 V, R_{Goff} = 1.1 Ω, T_{vj} = 150°C



正向偏压特性 二极管, D2 / D3 (典型)
forward characteristic of Diode, D2 / D3 (typical)
I_F = f (V_F)



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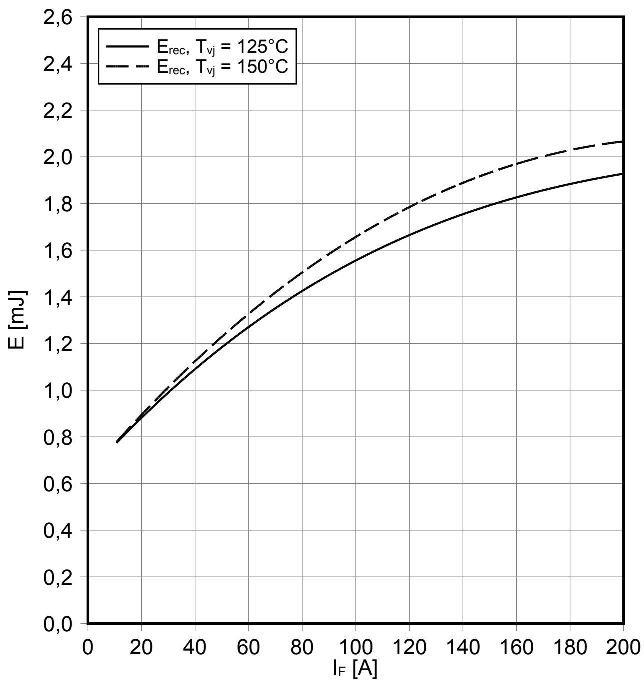
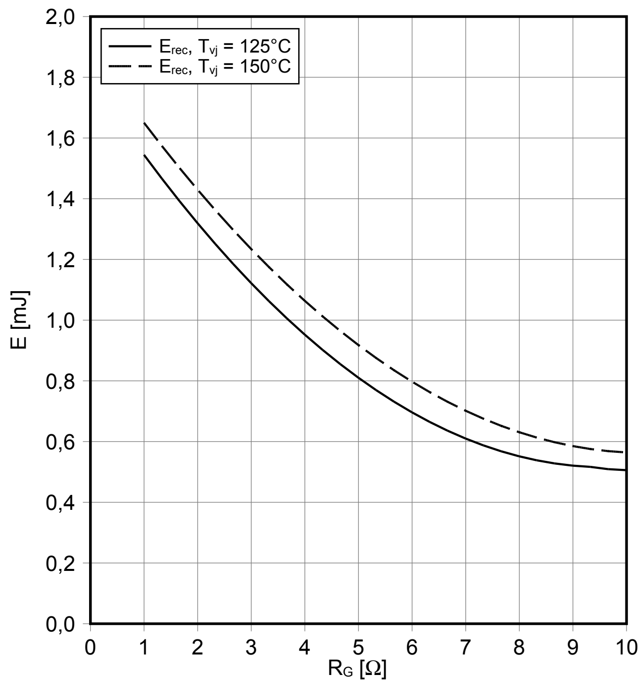
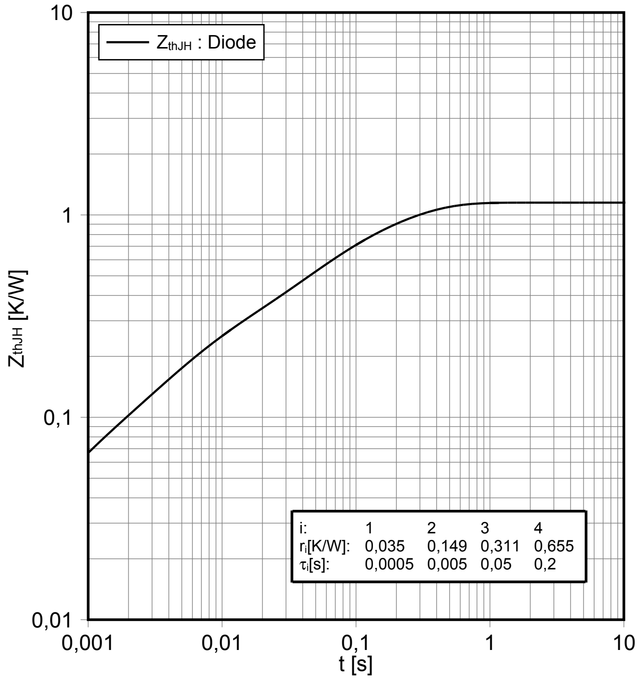
开关损耗 二极管, D2 / D3 （典型)
switching losses Diode, D2 / D3 (typical)
$E_{rec} = f(I_F)$
$R_{Gon} = 1.1\ \Omega$, $V_{CE} = 400$ V



开关损耗 二极管, D2 / D3 （典型)
switching losses Diode, D2 / D3 (typical)
$E_{rec} = f(R_G)$
$I_F = 100$ A, $V_{CE} = 400$ V

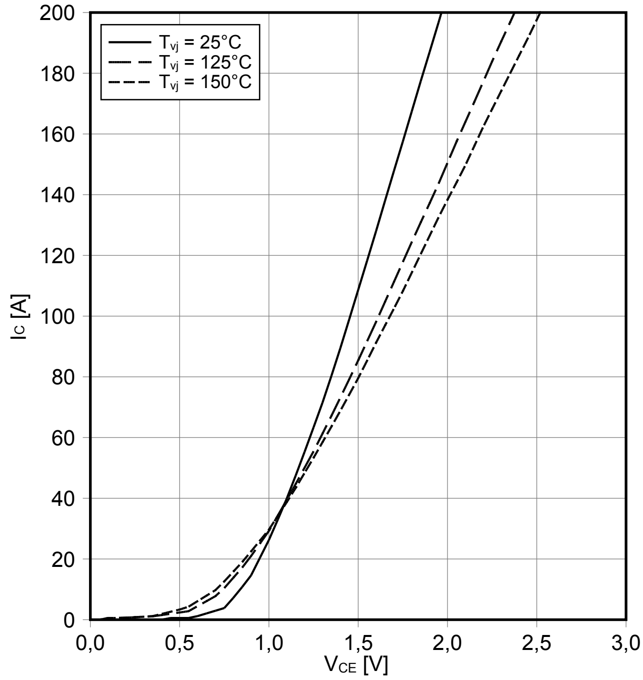


瞬态热阻抗 二极管, D2 / D3
transient thermal impedance Diode, D2 / D3
$Z_{thJH} = f(t)$

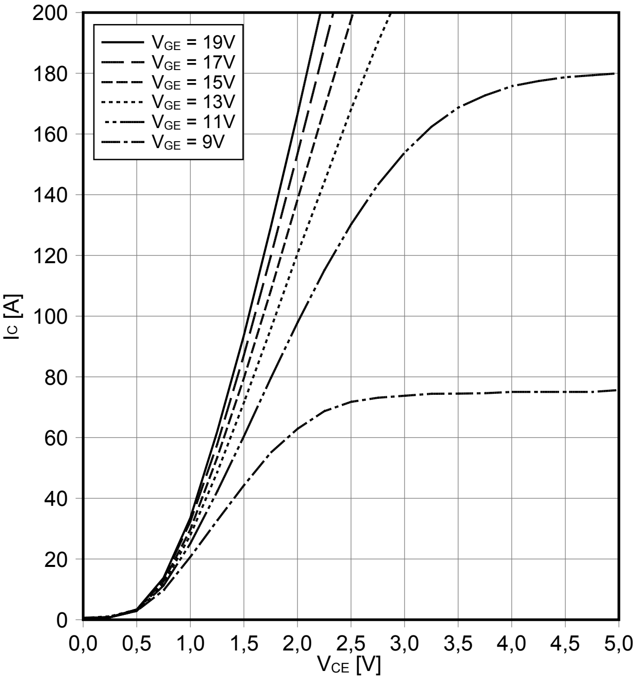


i:	1	2	3	4
r_i[K/W]:	0,035	0,149	0,311	0,655
τ_i[s]:	0,0005	0,005	0,05	0,2

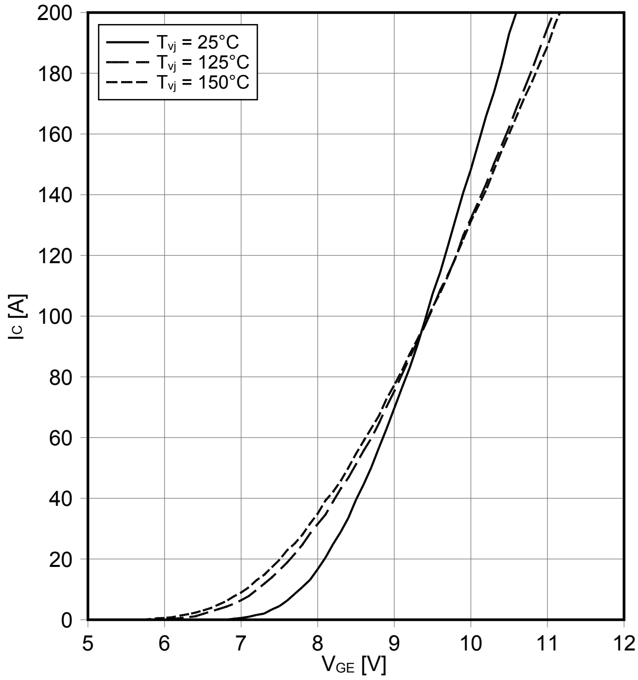
输出特性 IGBT, T2 / T3 （典型)
output characteristic IGBT, T2 / T3 (typical)
$I_C = f(V_{CE})$
$V_{GE} = 15$ V



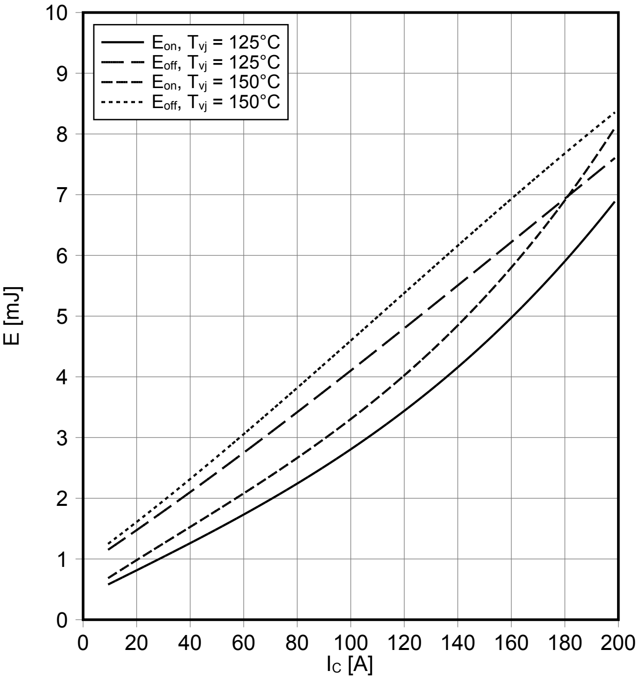
输出特性 IGBT, T2 / T3 （典型)
output characteristic IGBT, T2 / T3 (typical)
$I_C = f(V_{CE})$
$T_{vj} = 150°C$



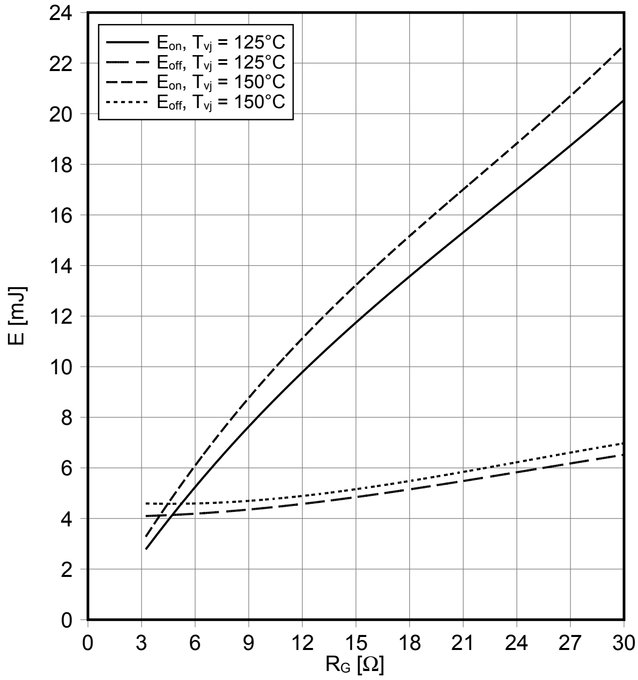
传输特性 IGBT, T2 / T3 (典型)
transfer characteristic IGBT, T2 / T3 (typical)
$I_C = f(V_{GE})$
$V_{CE} = 20$ V



开关损耗 IGBT, T2 / T3 （典型)
switching losses IGBT, T2 / T3 (typical)
$E_{on} = f(I_C)$, $E_{off} = f(I_C)$
$V_{GE} = \pm15$ V, $R_{Gon} = 3.3\ \Omega$, $R_{Goff} = 3.3\ \Omega$, $V_{CE} = 400$ V



开关损耗 IGBT, T2 / T3 （典型)
switching losses IGBT, T2 / T3 (typical)
$E_{on} = f(R_G)$, $E_{off} = f(R_G)$
$V_{GE} = \pm15$ V, $I_C = 100$ A, $V_{CE} = 400$ V



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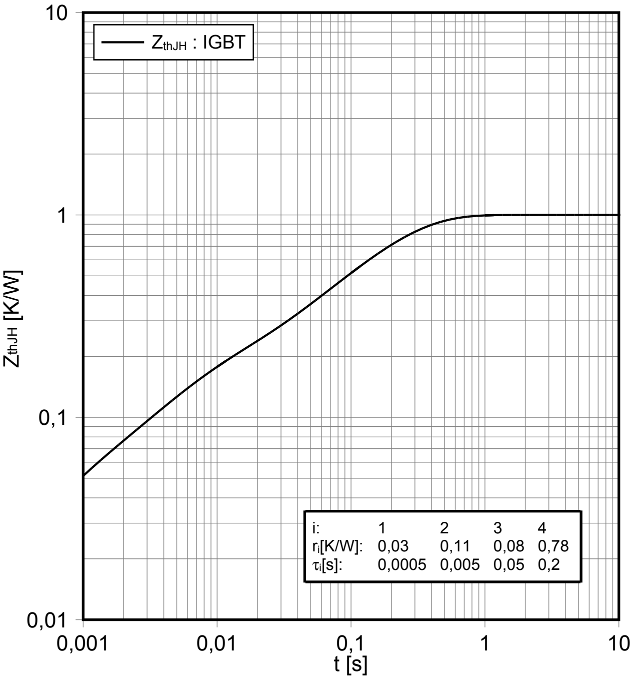
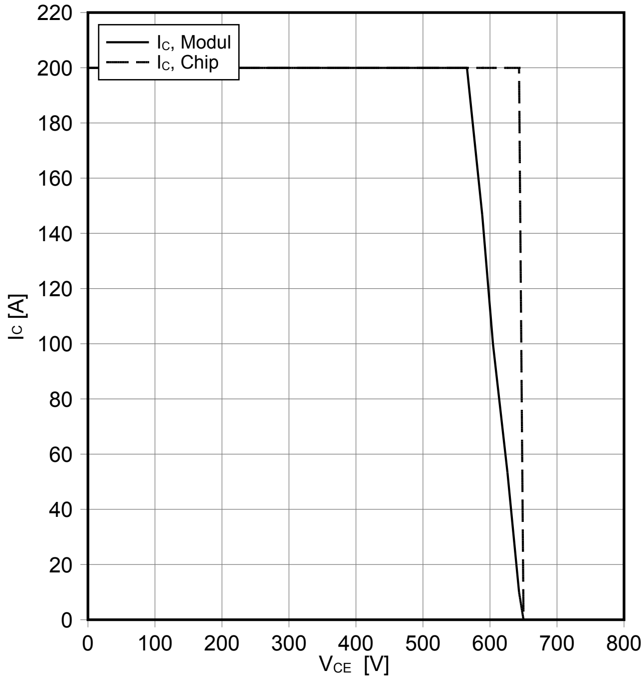
瞬态热阻抗 IGBT, T2 / T3
transient thermal impedance IGBT, T2 / T3
$Z_{thJH} = f(t)$

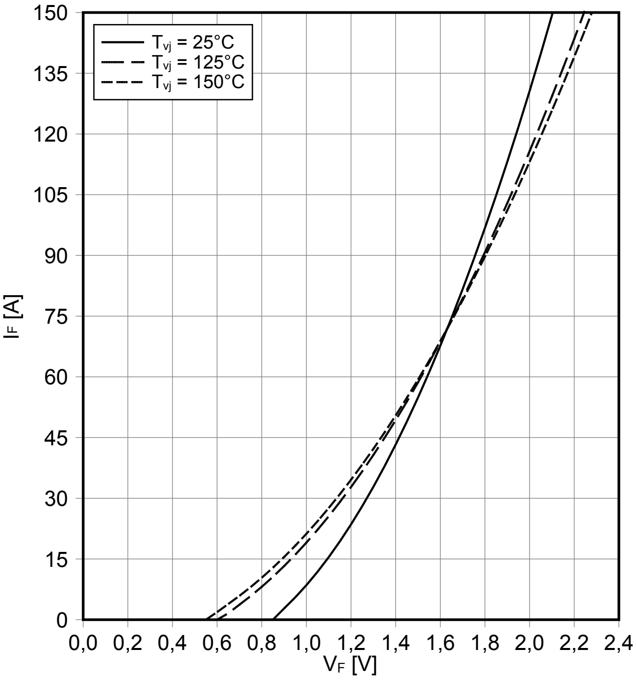


i:	1	2	3	4
r_i[K/W]:	0,03	0,11	0,08	0,78
τ_i[s]:	0,0005	0,005	0,05	0,2

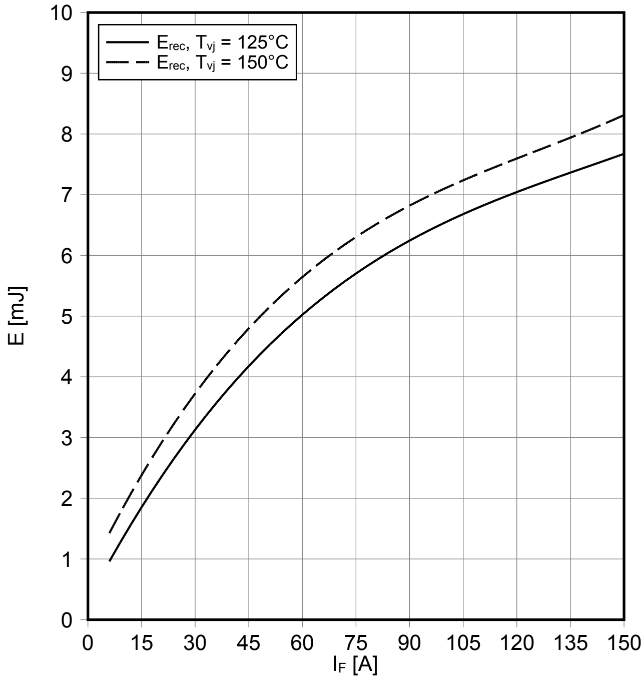
反偏安全工作区 IGBT, T2 / T3 （RBSOA）
reverse bias safe operating area IGBT, T2 / T3 (RBSOA)
$I_C = f(V_{CE})$
$V_{GE} = \pm 15$ V, $R_{Goff} = 3.3\ \Omega$, $T_{vj} = 150°C$



正向偏压特性 二极管, D1 / D4 （典型)
forward characteristic of Diode, D1 / D4 (typical)
$I_F = f(V_F)$



开关损耗 二极管, D1 / D4 （典型)
switching losses Diode, D1 / D4 (typical)
$E_{rec} = f(I_F)$
$R_{Gon} = 3.3\ \Omega$, $V_{CE} = 400$ V



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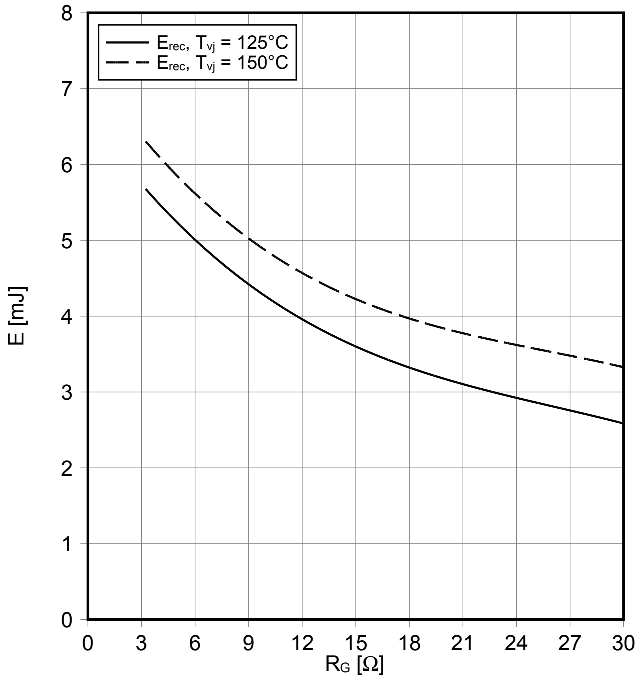
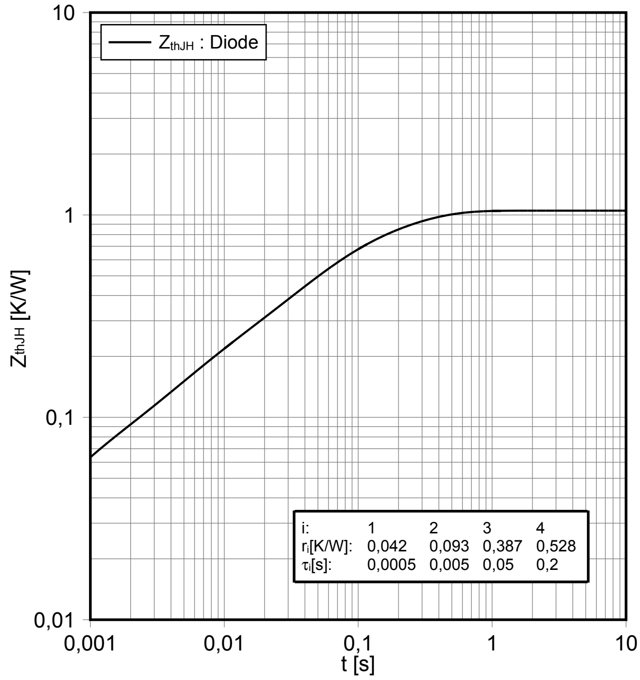
开关损耗 二极管, D1 / D4 （典型)
switching losses Diode, D1 / D4 (typical)
$E_{rec} = f(R_G)$
$I_F = 75$ A, $V_{CE} = 400$ V

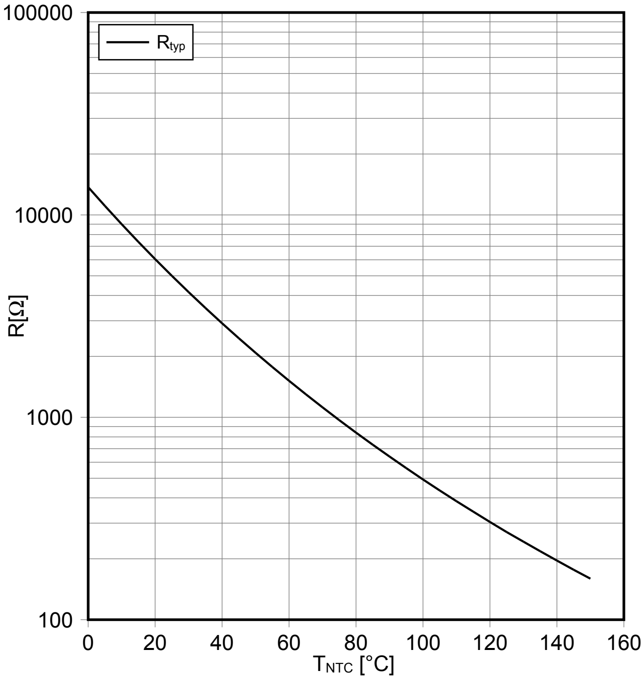


瞬态热阻抗 二极管, D1 / D4
transient thermal impedance Diode, D1 / D4
$Z_{thJH} = f(t)$



i:	1	2	3	4
r_i[K/W]:	0,042	0,093	0,387	0,528
τ_i[s]:	0,0005	0,005	0,05	0,2

负温度系数热敏电阻 温度特性
NTC-Thermistor-temperature characteristic (typical)
R = f (T)



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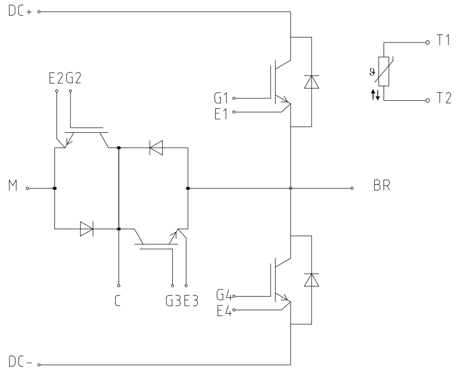
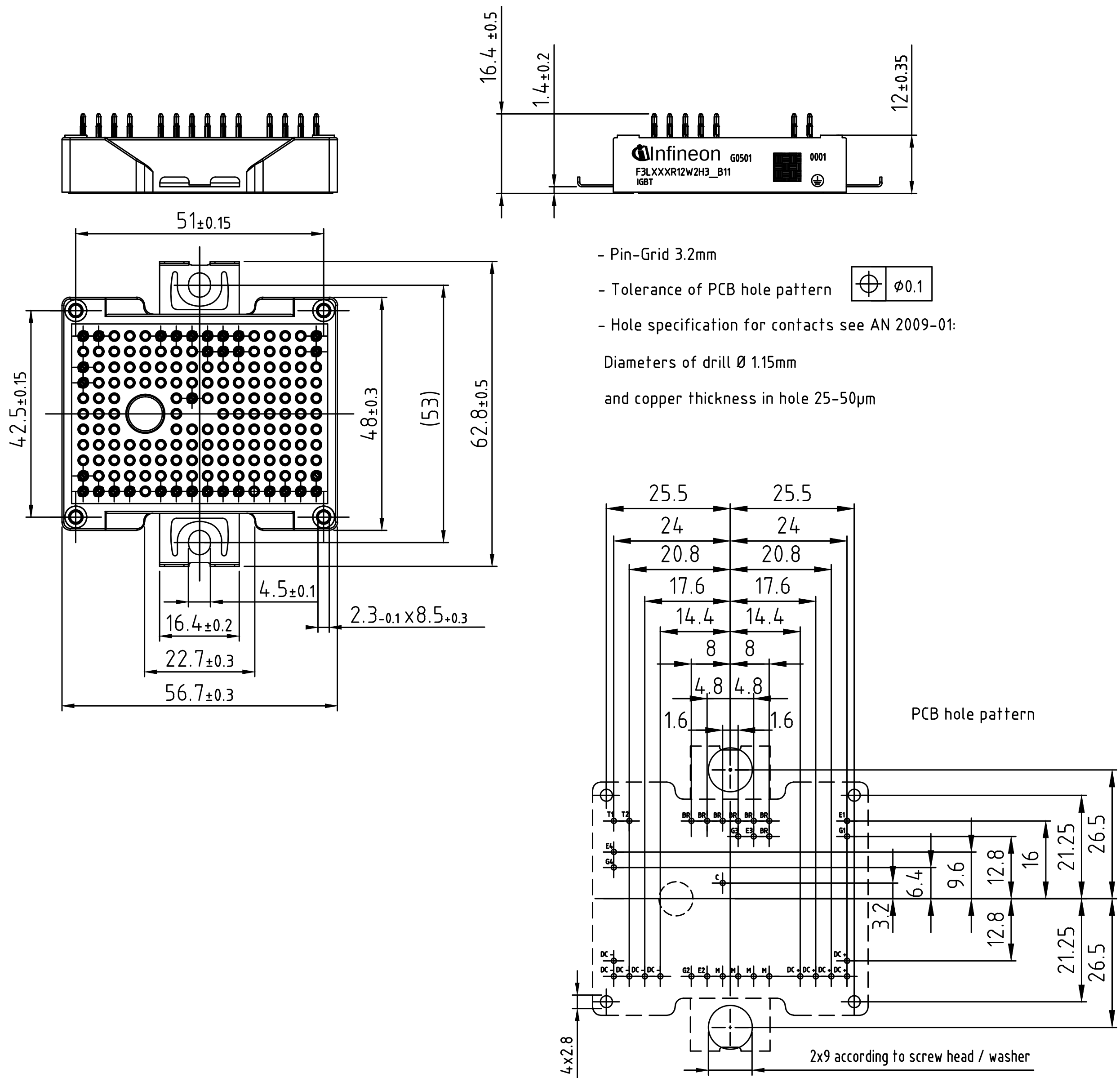
接线图 / Circuit diagram



封装尺寸 / Package outlines



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